



WM03N06M

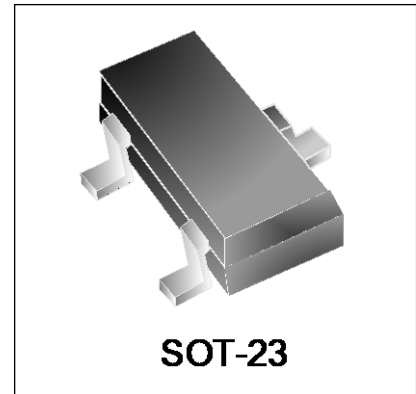
N-Channel Trench MOSFET

Features

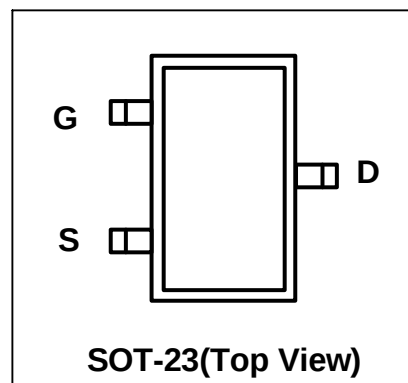
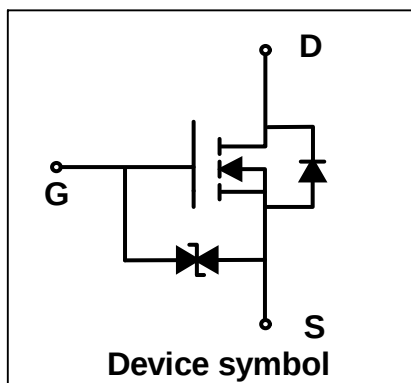
- $V_{DS} = 30V$, $I_D = 0.6A$
 $R_{DS(on)} < 0.50 \Omega @ V_{GS} = 4.5V$
 $R_{DS(on)} < 0.68 \Omega @ V_{GS} = 2.5V$
- Very Fast Switching
- Trench MOSFET Technology
- Pb Free Device
- ESD Protected

Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant



Schematic & PIN Configuration



Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Continuous Drain Current	I_D	600	mA
Gate-Source Voltage	V_{GS}	± 12	V
Power Dissipation ¹	P_D	350	mW
Pulsed Drain Current ²	I_{DM}	1.8	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^{\circ}C$
Junction-to-Ambient – Steady State ²	$R_{\theta JA}$	357	$^{\circ}C/W$

Electrical Characteristics (T_{amb}=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0 V, I _D = 250μA	30	-	-	V
Gate Threshold Voltage ³	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7	-	1.1	V
Drain Cut-off Current	I _{DSS}	V _{DS} =30 V, V _{GS} =0 V	-	-	1	μA
Gate leakage Current	I _{GSS}	V _{GS} =±12 V, V _{DS} =0 V	-	-	±10	μA
Drain-Source On-state Resistance ³	R _{DS(on)}	V _{GS} =4.5 V, I _D =600mA	-	0.31	0.50	Ω
		V _{GS} =2.5 V, I _D =300mA	-	0.40	0.68	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	-	40	-	pF
Output Capacitance	C _{oss}		-	8	-	
Reverse Transfer Capacitance	C _{rss}		-	3.5	-	
Switching Characteristics						
Total Gate Charge ⁴	Q _g	V _{DS} = 15V, V _{GS} = 4.5V, I _D = 1.0A	-	1.2	-	nC
Gate-Source Charge ⁴	Q _{gs}		-	0.3	-	
Gate-Drain Charge ⁴	Q _{gd}		-	0.28	-	
Turn-On Delay Time ⁴	t _{d(on)}	V _{DS} = 15V, V _{GEN} =4.5V, I _D = 6Ω, R _L = 15Ω	-	6.5	-	ns
Rise Time ⁴	t _r		-	9.5	-	
Turn-Off Delay Time ⁴	t _{d(off)}		-	24	-	
Fall Time ⁴	t _f		-	35	-	
Drain-Source Body Diode Characteristics						
Diode Forward Voltage	V _{SD}	I _S =600mA, V _{GS} =0V	-	-	1.2	V

Notes:

1. Surface Mounted on FR4 Board, t_s≤10 sec.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. Pulse Test : Pulse Width≤380μs, Duty Cycle≤0.5%.
4. Guaranteed by design, not subject to production testing.

Typical Characteristics

Figure 1. Output Characteristics

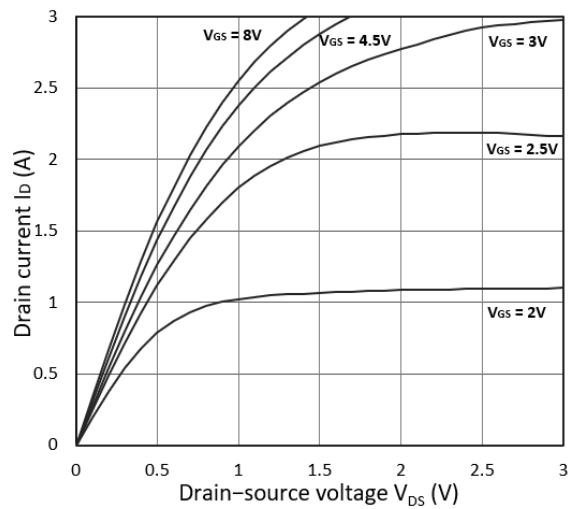


Figure 2. Transfer Characteristics

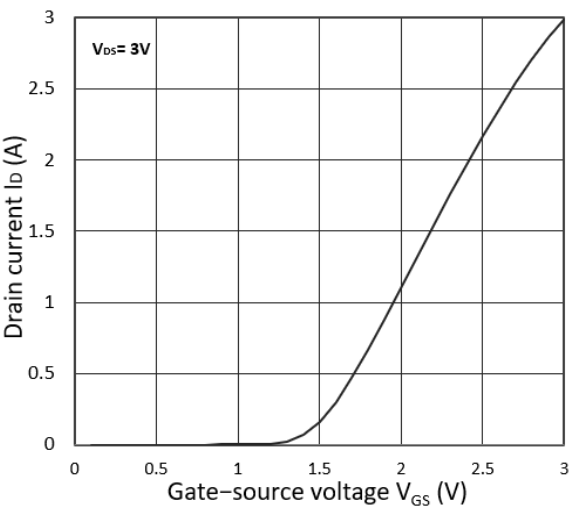


Figure 3. $R_{DS(on)}$ vs. I_D

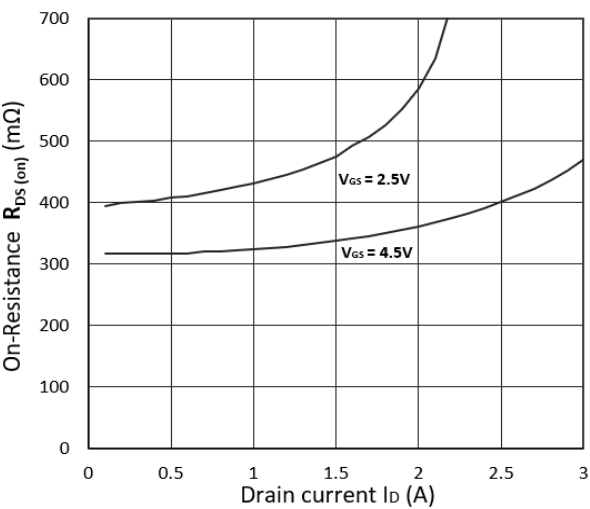


Figure 4. $R_{DS(on)}$ vs. V_{GS}

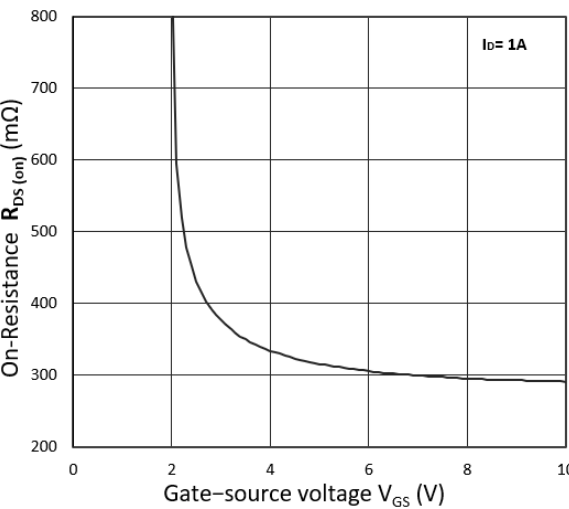


Figure 5. I_S vs. V_{SD}

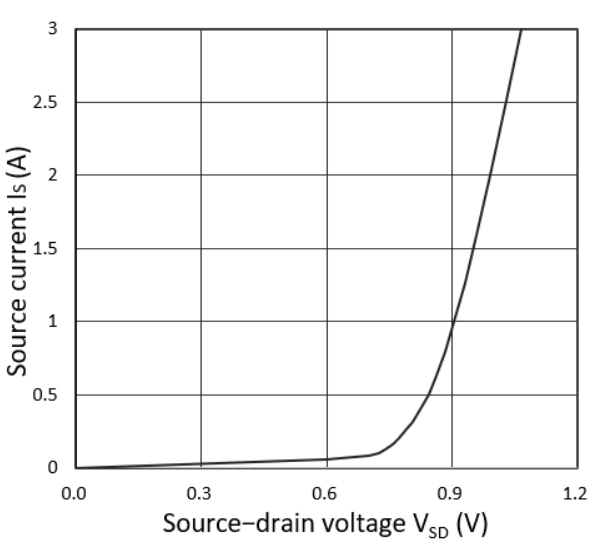
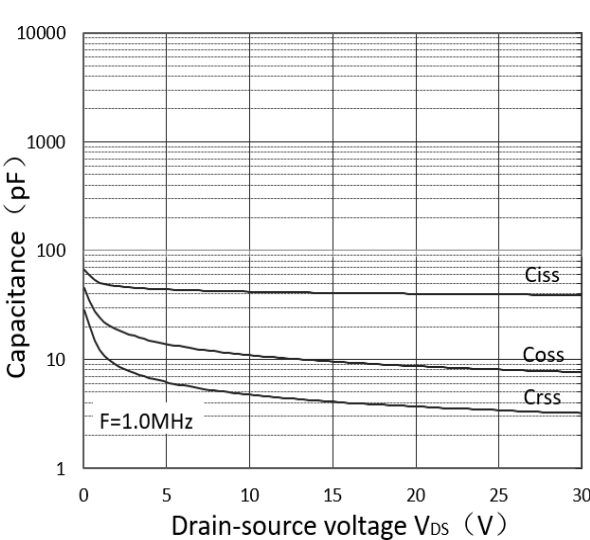
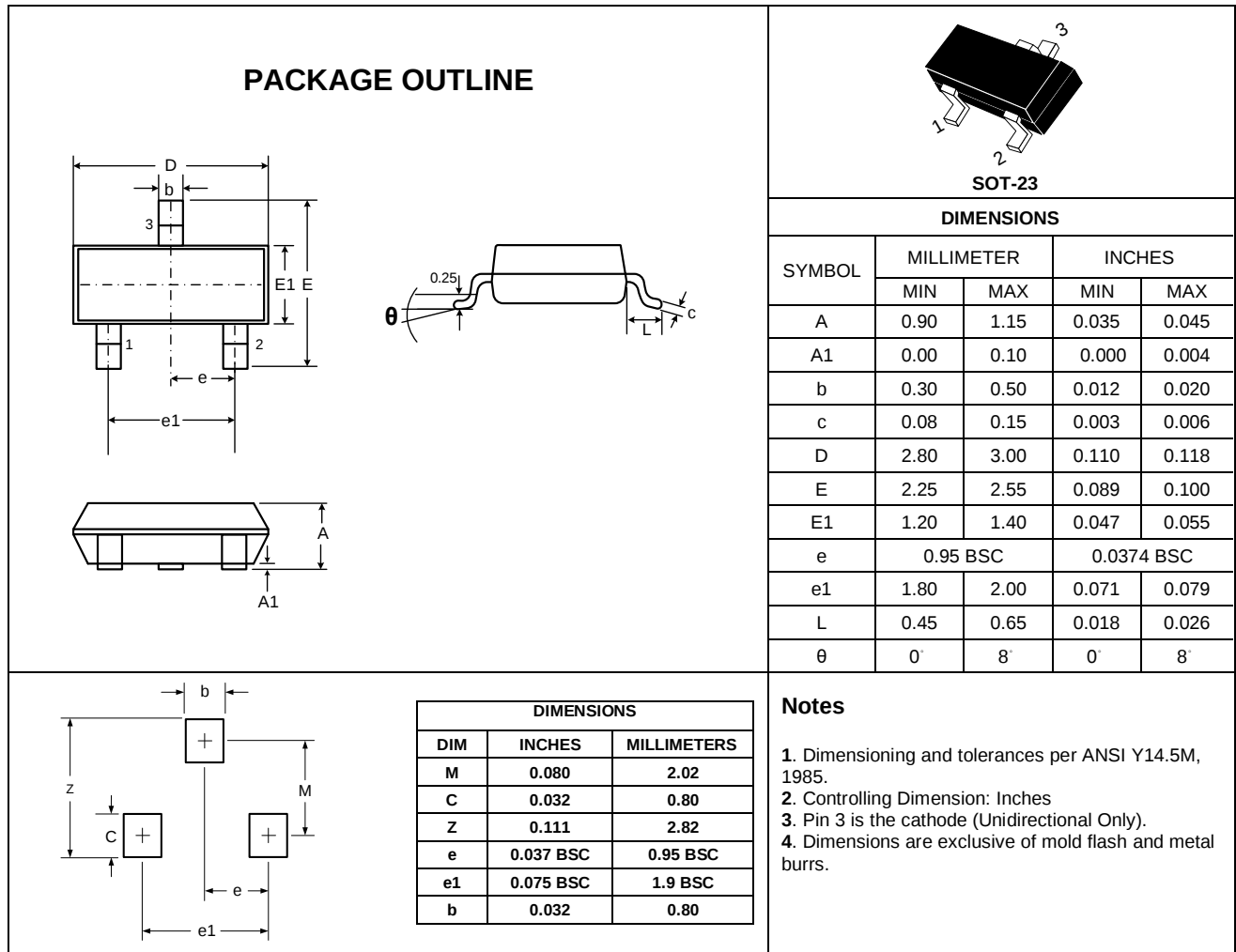


Figure 6. Capacitance Characteristics



Outline Drawing – SOT-23



Marking Codes

Part Number	WM03N06M
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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For additional information, please contact your local Sales Representative.



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The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time. Users should verify actual device performance in their specific applications.